

BSS84L, BVSS84L

Power MOSFET Single P-Channel SOT-23 -50 V, 10 Ω

- SOT-23 Surface Mount Package Saves Board Space
- BV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	50	Vdc
Gate-to-Source Voltage – Continuous	V_{GS}	± 20	Vdc
Drain Current Continuous @ $T_A = 25^\circ\text{C}$ Pulsed Drain Current ($t_p \leq 10 \mu\text{s}$)	I_D I_{DM}	130 520	mA
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	225	mW
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Thermal Resistance – Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	T_L	260	$^\circ\text{C}$

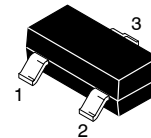
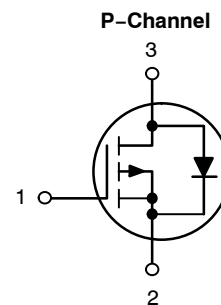
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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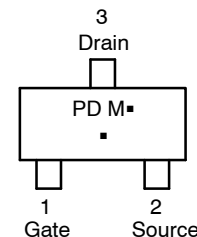
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$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$
-50 V	10 Ω @ 10 V



SOT-23
CASE 318
STYLE 21

MARKING DIAGRAM & PIN ASSIGNMENT



PD = Specific Device Code
M = Date Code
■ = Pb-Free Package

(*Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
BSS84LT1G, BVSS84LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
BSS84LT7G	SOT-23 (Pb-Free)	3,500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-to-Source Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = -250\text{ }\mu\text{Adc}$)	$V_{(BR)DSS}$	-50	-	-	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = -25\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$) ($V_{DS} = -50\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$) ($V_{DS} = -50\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$, $T_J = 125^\circ\text{C}$)	I_{DSS}	-	-	-0.1 -15 -60	μAdc
Gate-Body Leakage Current ($V_{GS} = \pm 20\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	-	-	± 10	nAdc

ON CHARACTERISTICS (Note 1)

Gate-Source Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$)	$V_{GS(th)}$	-0.9	-	-2.0	Vdc
Static Drain-to-Source On-Resistance ($V_{GS} = -5.0\text{ Vdc}$, $I_D = -100\text{ mAdc}$)	$R_{DS(on)}$	-	4.7	10	Ω
Transfer Admittance ($V_{DS} = -25\text{ Vdc}$, $I_D = -100\text{ mAdc}$, $f = 1.0\text{ kHz}$)	$ Y_{fs} $	50	-	-	mS

DYNAMIC CHARACTERISTICS

Input Capacitance	$V_{DS} = 5.0\text{ Vdc}$	C_{iss}	-	36	-	pF
Output Capacitance	$V_{DS} = 5.0\text{ Vdc}$	C_{oss}	-	17	-	
Transfer Capacitance	$V_{DG} = 5.0\text{ Vdc}$	C_{rss}	-	6.5	-	

SWITCHING CHARACTERISTICS (Note 2)

Turn-On Delay Time	$V_{DD} = -15\text{ Vdc}$, $I_D = -2.5\text{ Adc}$, $R_L = 50\text{ }\Omega$	$t_{d(on)}$	-	3.6	-	ns
Rise Time		t_r	-	9.7	-	
Turn-Off Delay Time		$t_{d(off)}$	-	12	-	
Fall Time		t_f	-	1.7	-	
Gate Charge	$V_{DD} = -40\text{ Vdc}$, $I_D = -0.5\text{ A}$, $V_{GS} = -10\text{ V}$	Q_T	-	2.2	-	nC

SOURCE-DRAIN DIODE CHARACTERISTICS

Continuous Current		I_S	-	-	-0.130	A
Pulsed Current		I_{SM}	-	-	-0.520	
Forward Voltage (Note 2)	$V_{GS} = 0\text{ V}$, $I_S = -130\text{ mA}$	V_{SD}	-	-	-2.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.
2. Switching characteristics are independent of operating junction temperature.

TYPICAL ELECTRICAL CHARACTERISTICS

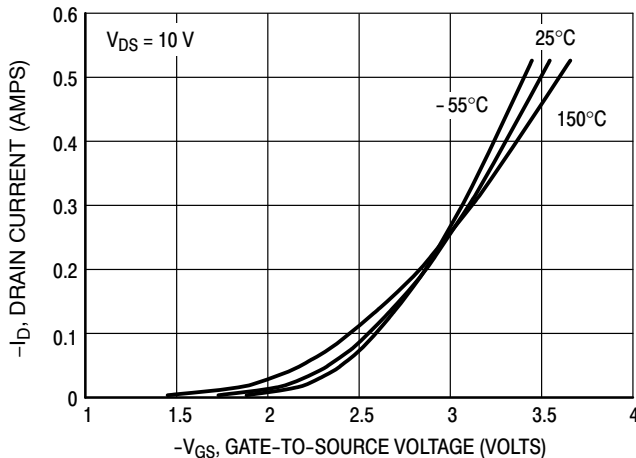


Figure 1. Transfer Characteristics

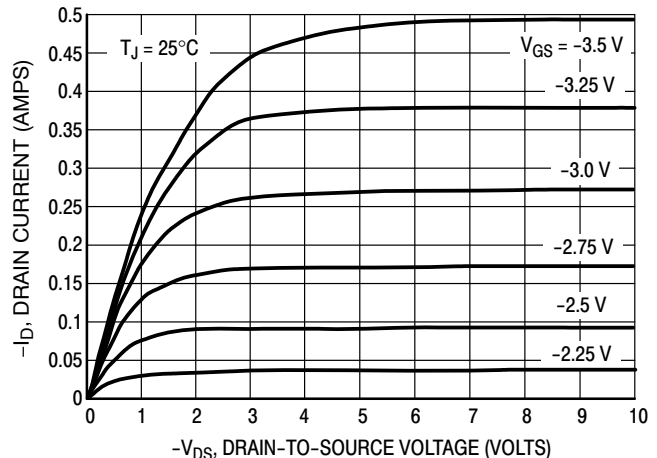


Figure 2. On-Region Characteristics

TYPICAL ELECTRICAL CHARACTERISTICS

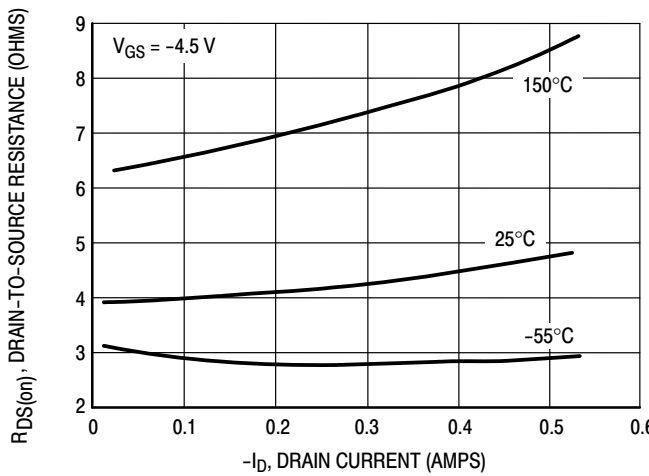


Figure 3. On-Resistance versus Drain Current

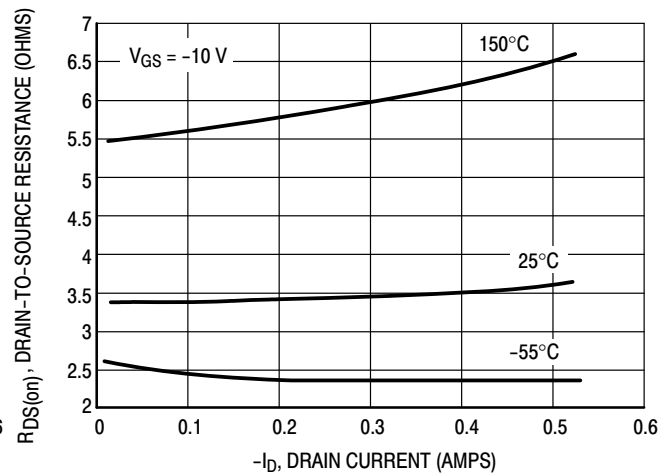


Figure 4. On-Resistance versus Drain Current

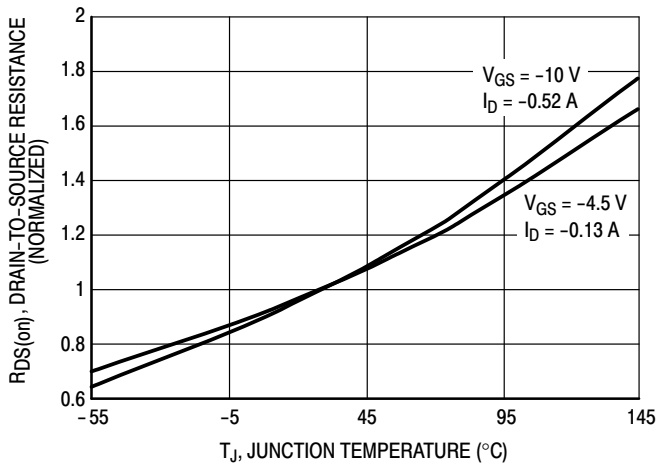


Figure 5. On-Resistance Variation with Temperature

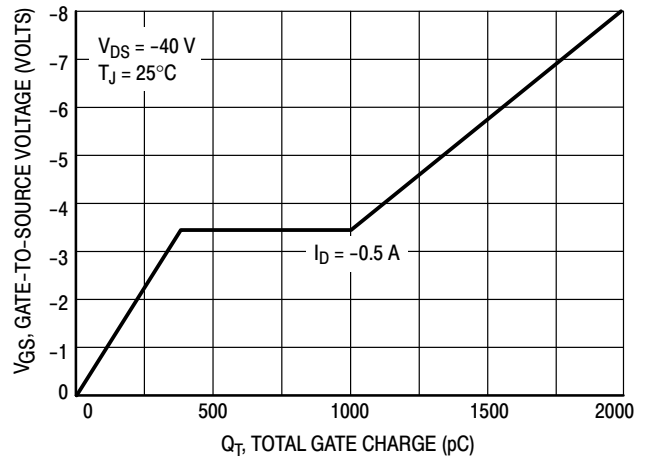


Figure 6. Gate Charge

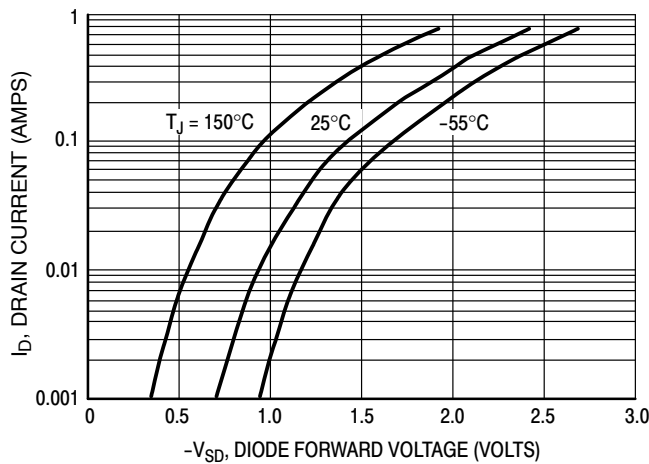


Figure 7. Body Diode Forward Voltage

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